

CentralTM Semiconductor Corp.

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Manufacturers of World Class Discrete Semiconductors

2N3458
2N3459
2N3460

N-CHANNEL JUNCTION
FIELD EFFECT TRANSISTOR

JEDEC TO-18 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR 2N3458, 2N3459, 2N3460 types are silicon N-Channel Junction Field Effect Transistors designed for low frequency, low noise amplifier applications.

MAXIMUM RATINGS (T_A = 25°C)

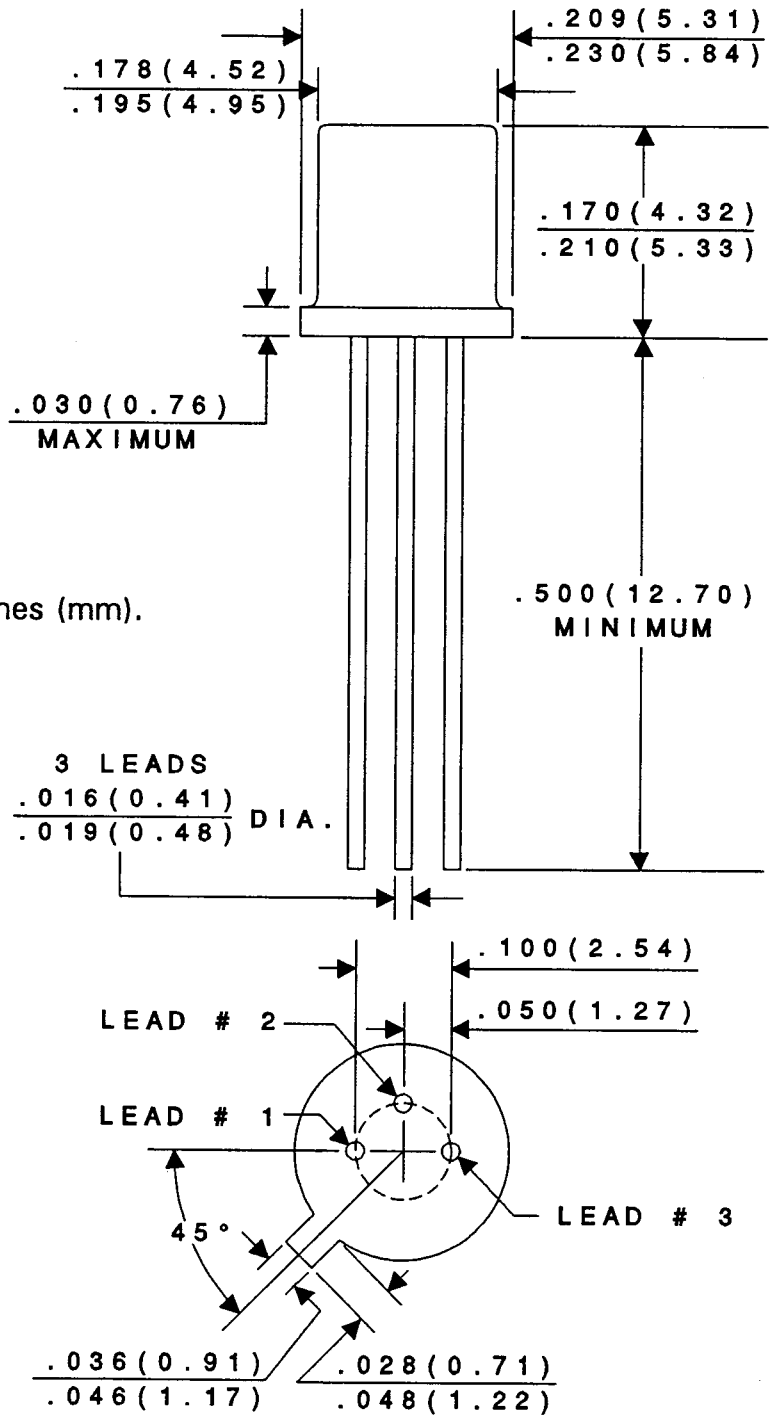
	SYMBOL		UNITS
Drain-Gate Voltage	V _{DG}	50	V
Gate-Source Voltage	V _{GS}	50	V
Gate Current	I _G	10	mA
Power Dissipation	P _D	300	mW
Storage Temperature	T _{stg}	-65 to +175	°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	2N3458		2N3459		2N3460		UNITS
		MIN	MAX	MIN	MAX	MIN	MAX	
I _{GSS}	V _{GS} = 30V		0.25		0.25		0.25	nA
I _{DSS}	V _{DS} = 20V	3.0	15	0.8	4.0	0.2	1.0	mA
BV _{GSS}	I _G = 1.0μA	50		50		50		V
V _{GS(OFF)}	V _{DS} = 20V, I _D = 1.0μA		7.8		3.4		1.8	V
Y _{fs}	V _{DS} = 20V, f = 1.0kHz	2500	10000	1500	6000	800	4500	μmhos
Y _{os}	V _{DS} = 30V, f = 1.0kHz		35		20		5.0	μmhos
C _{iss}	V _{DS} = 10V		18		18		18	pF
C _{oss}	V _{DS} = 30V		5.0		5.0		5.0	pF
NF	V _{DS} = 10V, f = 20Hz, R _G = 1.0MΩ		6.0		4.0		4.0	dB

(OVER)

JEDEC TO-18 CASE - MECHANICAL OUTLINE



All Dimensions in Inches (mm).

LEAD CODE:

- 1) SOURCE
- 2) DRAIN
- 3) GATE